# 4V Drive Nch MOS FET **RHK005N03**

#### ●Structure

Silicon N-channel MOS FET

## ● Features

- 1) Low On-resistance.
- 2) High speed switching.

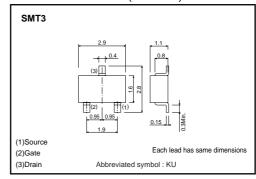
## Applications

Switching

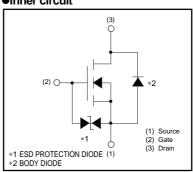
## ●Packaging specifications and hFE

	Package	Taping
Type	Code	T146
	Basic ordering unit (pieces)	3000
RHK005N0	0	

## ●External dimensions (Unit : mm)



## ●Inner circuit



## ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{\text{DSS}}$	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±500	mA
	Pulsed	IDP *1	±2.0	Α
Total power dissipation		P <sub>D</sub> *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

#### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

<sup>\*</sup> Each terminal mounted on a recommended land

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Each terminal mounted on a recommended land

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	1	_	±10	μΑ	Vgs= ±20V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	٧	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	٧	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	_	350	550	$m\Omega$	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 10V
		-	510	720	mΩ	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 4.5V
		-	600	840	mΩ	Ip= 500mA, Vgs= 4V
Forward transfer admittance	Yfs *	0.5	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA
Input capacitance	Ciss	_	45	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	20	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	10	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	10	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	10	_	ns	ID= 250mA
Turn-off delay time	t <sub>d (off)</sub> *	-	15	_	ns	V <sub>GS</sub> = 10V R <sub>L</sub> =60Ω
Fall time	t <sub>f</sub> *	_	30	_	ns	R <sub>G</sub> =10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	-	1.2	V	I <sub>S</sub> = 0.16A, V <sub>GS</sub> =0V

### Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any
  means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the
  product described in this document are for reference only. Upon actual use, therefore, please request
  that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or
  otherwise dispose of the same, no express or implied right or license to practice or commercially
  exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

#### About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.

In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.

